BSS84

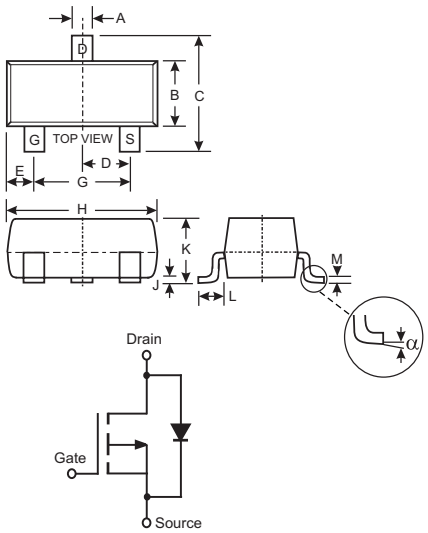
P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free/RoHS Compliant (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT-23
- Case Material: UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish).
- Terminal Connections: See Diagram
- Marking (See Page 2): K84
- Ordering & Date Code Information: See Page 2
- Weight: 0.008 grams (approximate)



SOT-23		
Dim	**Min**	**Max**
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ T_A = 25°C unless otherwise specified

eristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	-50	V
Drain-Gate Voltage $R_{GS} \leq 20K\Omega$		V_{DGR}	-50	V
Gate-Source Voltage	Continuous	V_{GSS}	±20	V
Drain Current (Note 1)	Continuous	I_D	-130	mA
Total Power Dissipation (Note 1)		P_d	300	mW
Thermal Resistance, Junction to Ambient		$R_{\theta JA}$	417	°C/W
Operating and Storage Temperature Range		T_j, T_{STG}	-55 to +150	°C

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)						
Drain-Source Breakdown Voltage	BV_{DSS}	-50	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	— — —	— — —	-15 -60 -100	µA µA nA	V_{DS} = -50V, V_{GS} = 0V, T_J = 25°C V_{DS} = -50V, V_{GS} = 0V, T_J = 125°C V_{DS} = -25V, V_{GS} = 0V, T_J = 25°C
Gate-Body Leakage	I_{GSS}	—	—	±10	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.8	—	-2.0	V	V_{DS} = V_{GS}, I_D = -1mA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	—	10	Ω	V_{GS} = -5V, I_D = -0.100A
Forward Transconductance	g_{FS}	0.05	—	—	S	V_{DS} = -25V, I_D = -0.1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	—	45	pF	V_{DS} = -25V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	12	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(ON)}$	—	10	—	ns	V_{DD} = -30V, I_D = -0.27A, R_{GEN} = 50Ω, V_{GS} = -10V
Turn-Off Delay Time	$t_{D(OFF)}$	—	18	—	ns	

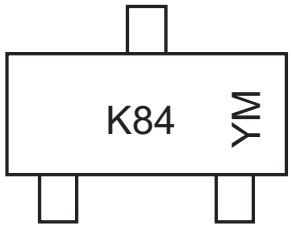
Note: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
2. Short duration test pulse used to minimize self-heating effect.
3. No purposefully added lead.

Ordering Information (Note 4)

Device	Packaging	Shipping
BSS84-7-F	SOT-23	3000/Tape & Reel

Notes: 4. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K84 = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: N = 2002
M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

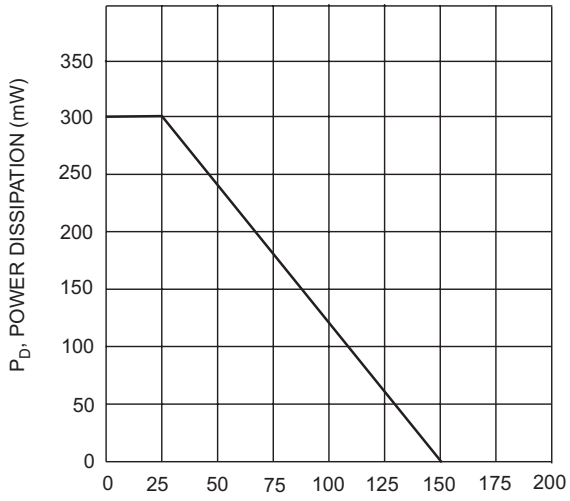


Fig. 1, Max Power Dissipation vs Ambient Temperature

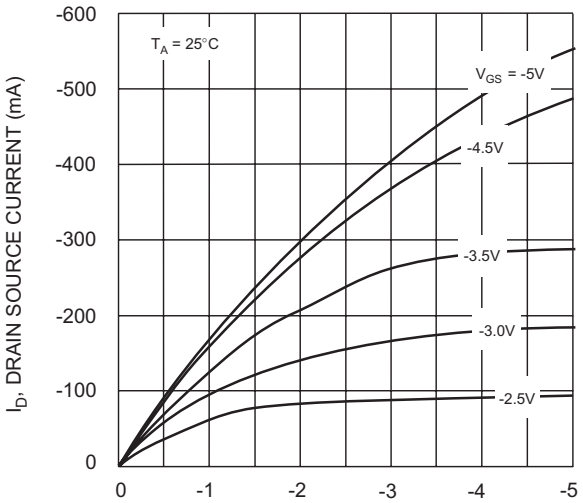


Fig. 2, Drain Source Current vs. Drain Source Voltage

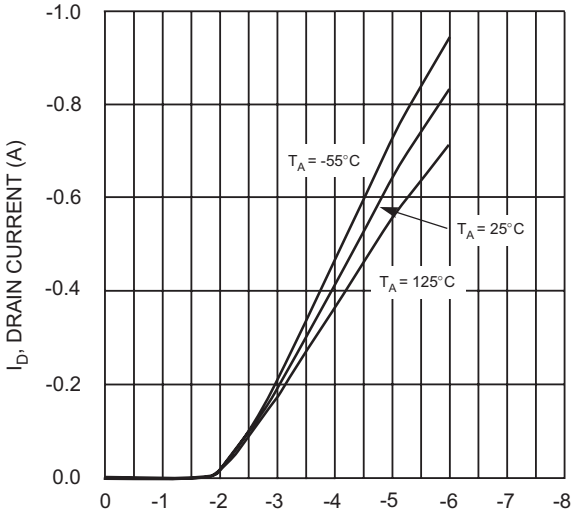


Fig. 3, Drain Current vs. Gate Source Voltage

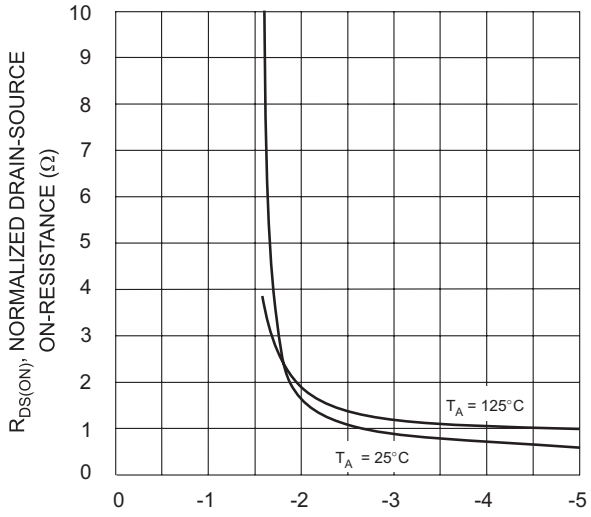


Fig. 4, On Resistance vs. Gate Source Voltage

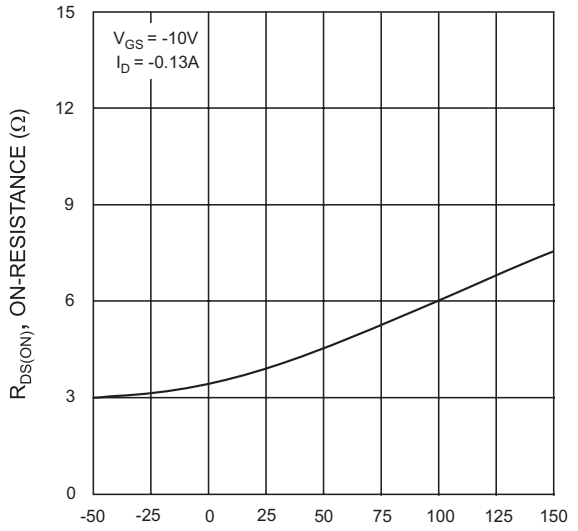


Fig. 5, On-Resistance vs. Junction Temperature

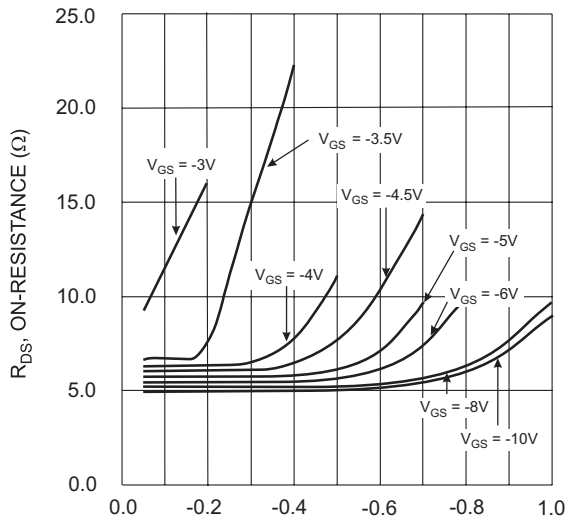


Fig. 6, On-Resistance vs. Drain Current